



100V 105mΩ N-Ch Power MOSFET

Features

- Low $R_{DS(ON)}$
- Low Gate Charge
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

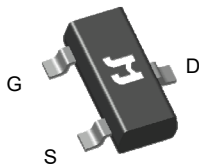
Applications

- Power Management in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC Sub-systems

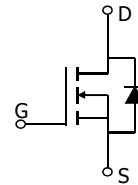
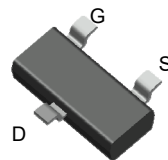
Product Summary

Parameter	Value	Unit
V_{DS}	100	V
$V_{GS(th_Typ)}$	1.9	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	1.8	A
$R_{DS(ON_Typ)}$ (@ $V_{GS} = 10V$)	105	mΩ
$R_{DS(ON_Typ)}$ (@ $V_{GS} = 4.5V$)	139	mΩ

SOT-23 Top View



SOT-23 Bottom View

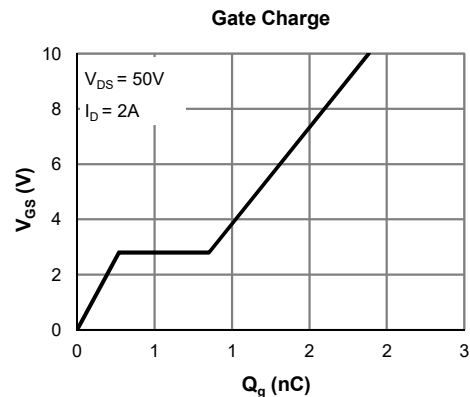
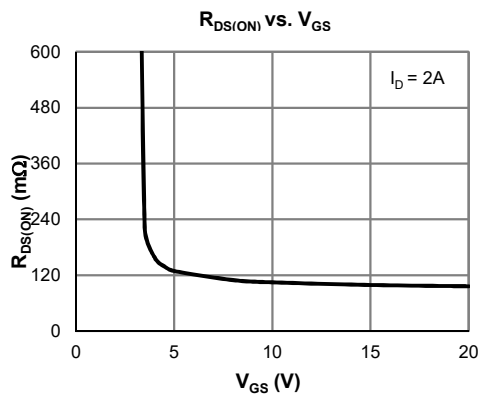


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSL10130AL-7	SOT-23	3	1013	3	-55 to 150	7-inch Reel	3000

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_A = 25^\circ C$	1.8
		$T_A = 70^\circ C$	1.4
Pulsed Drain Current ⁽²⁾	I_{DM}	17.0	A
Avalanche Current ⁽³⁾	I_{AS}	4.0	A
Avalanche Energy ⁽³⁾	E_{AS}	0.80	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_A = 25^\circ C$	0.72
		$T_A = 70^\circ C$	0.46
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C



**Electrical Characteristics** (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

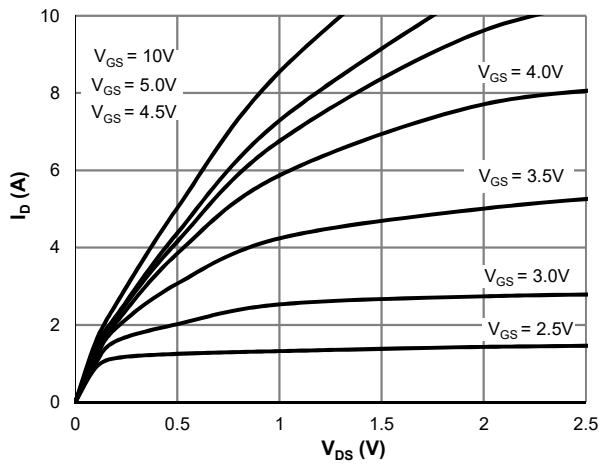
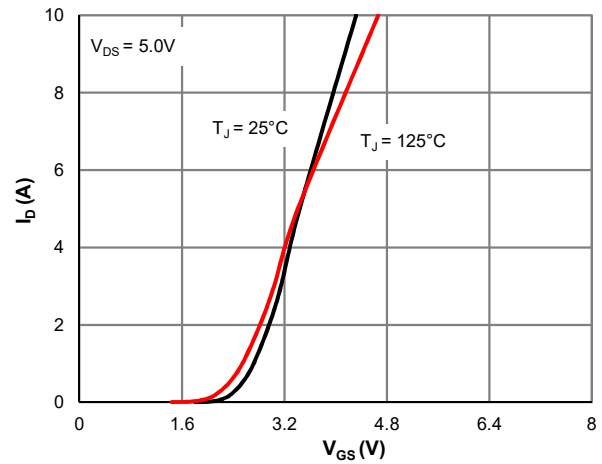
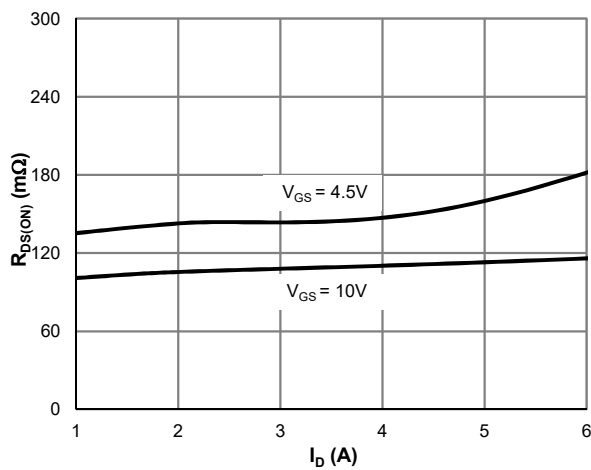
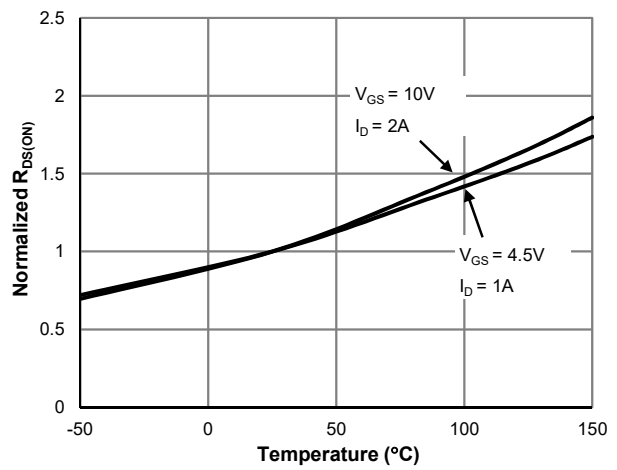
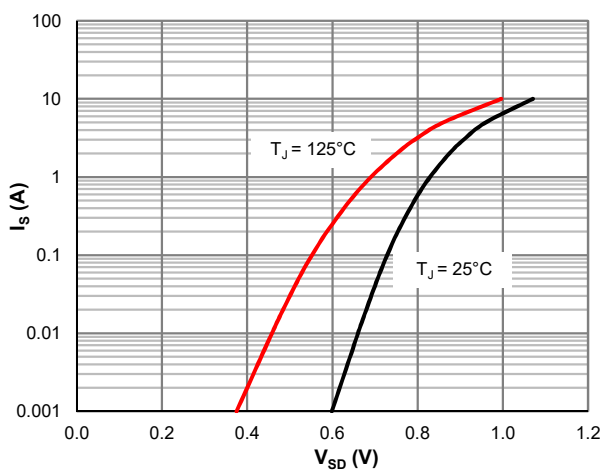
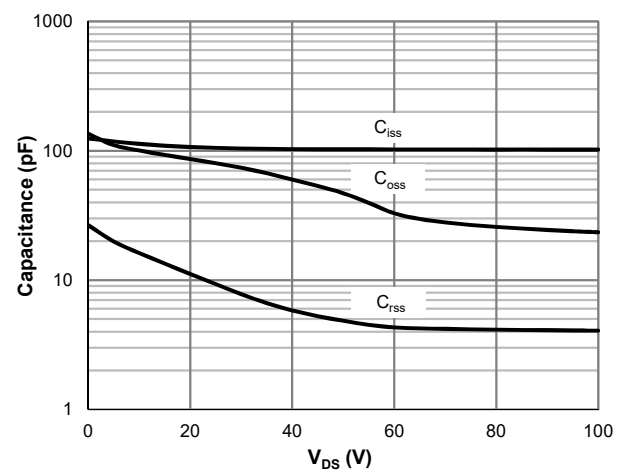
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1.2	1.9	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 2\text{A}$		105	131	$\text{m}\Omega$
	$R_{DS(on)}$	$V_{GS} = 4.5\text{V}$, $I_D = 1\text{A}$		139	174	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}$, $I_D = 2\text{A}$		6.8		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}$, $V_{GS} = 0\text{V}$		0.70	1.0	V
Diode Continuous Current	I_S	$T_A = 25^\circ\text{C}$			0.7	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 50\text{V}$, $f = 1\text{MHz}$		103		pF
Output Capacitance	C_{oss}			47		pF
Reverse Transfer Capacitance	C_{rss}			4.9		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$		2.6		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0$ to 10V $V_{DS} = 50\text{V}$, $I_D = 2\text{A}$		2.3		nC
Total Gate Charge (@ $V_{GS} = 4.5\text{V}$)	Q_g			1.3		nC
Gate Source Charge	Q_{gs}			0.3		nC
Gate Drain Charge	Q_{gd}			0.7		nC
Turn-On Delay Time	$t_{D(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$ $R_L = 25\Omega$, $R_{GEN} = 6\Omega$		2.1		ns
Turn-On Rise Time	t_r			3.3		ns
Turn-Off Delay Time	$t_{D(off)}$			7.5		ns
Turn-Off Fall Time	t_f			3.2		ns
Body Diode Reverse Recovery Time	t_{rr}		$I_F = 2\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		21	
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 2\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		8.0		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	144	173	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 100\mu\text{H}$, $V_{GS} = 10\text{V}$, $V_{DS} = 50\text{V}$] while its value is limited by $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: Body-Diode Characteristics

Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

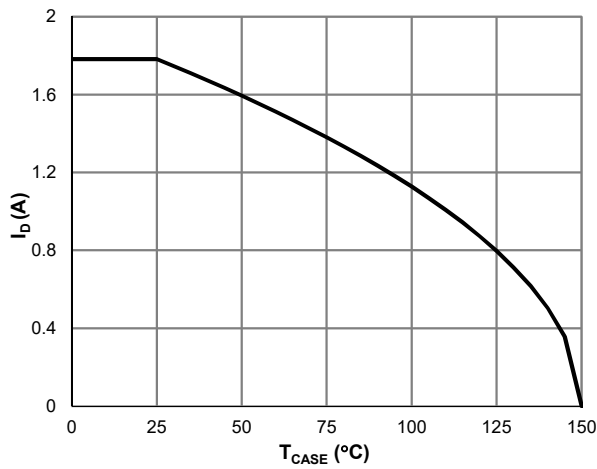


Figure 7: Current De-rating

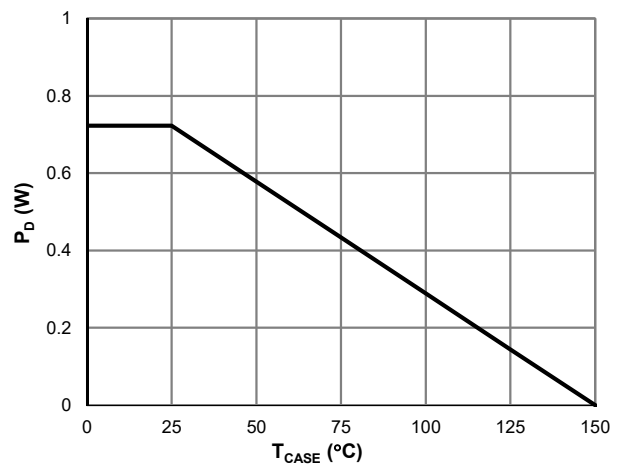


Figure 8: Power De-rating

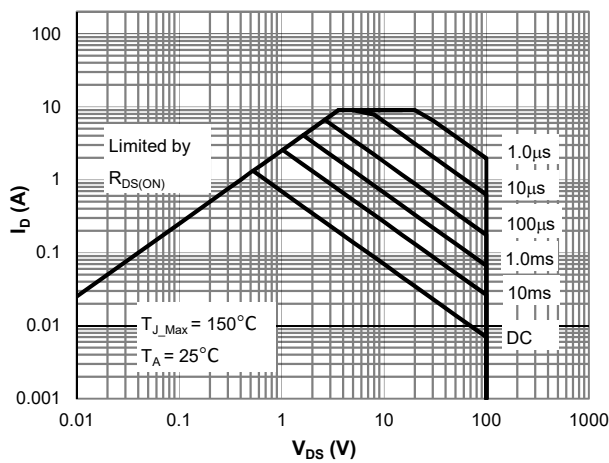


Figure 9: Maximum Safe Operating Area

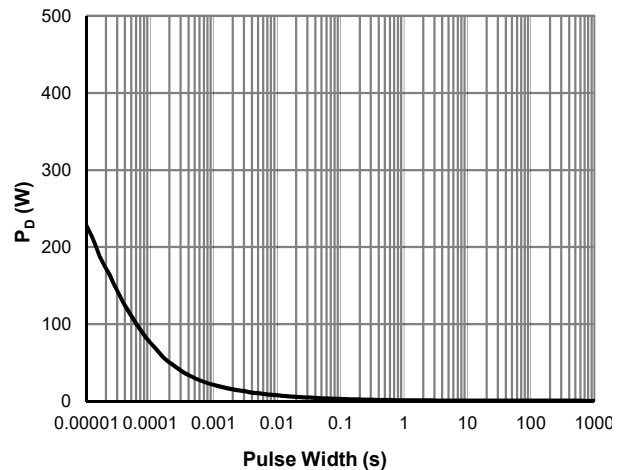


Figure 10: Single Pulse Power Rating, Junction-to-Case

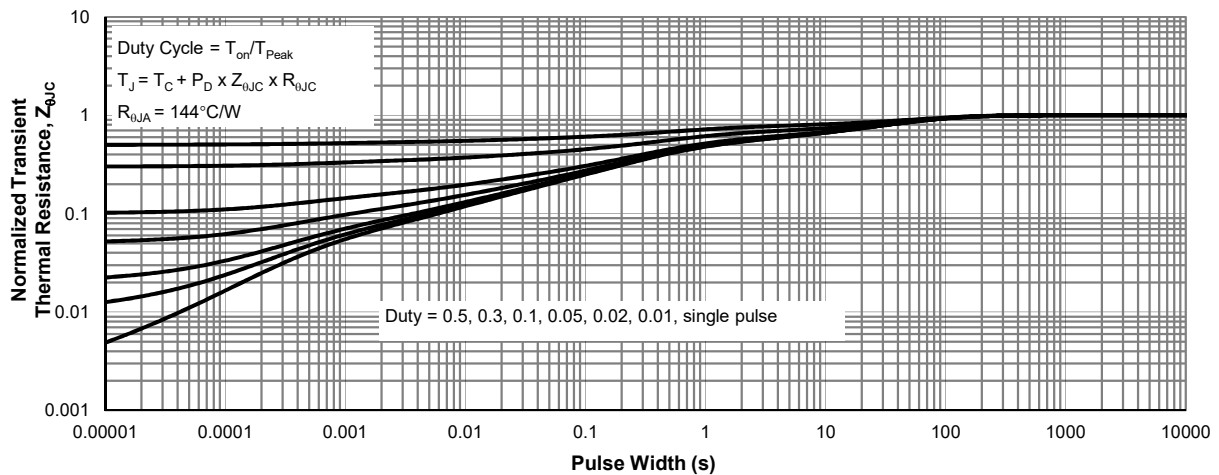
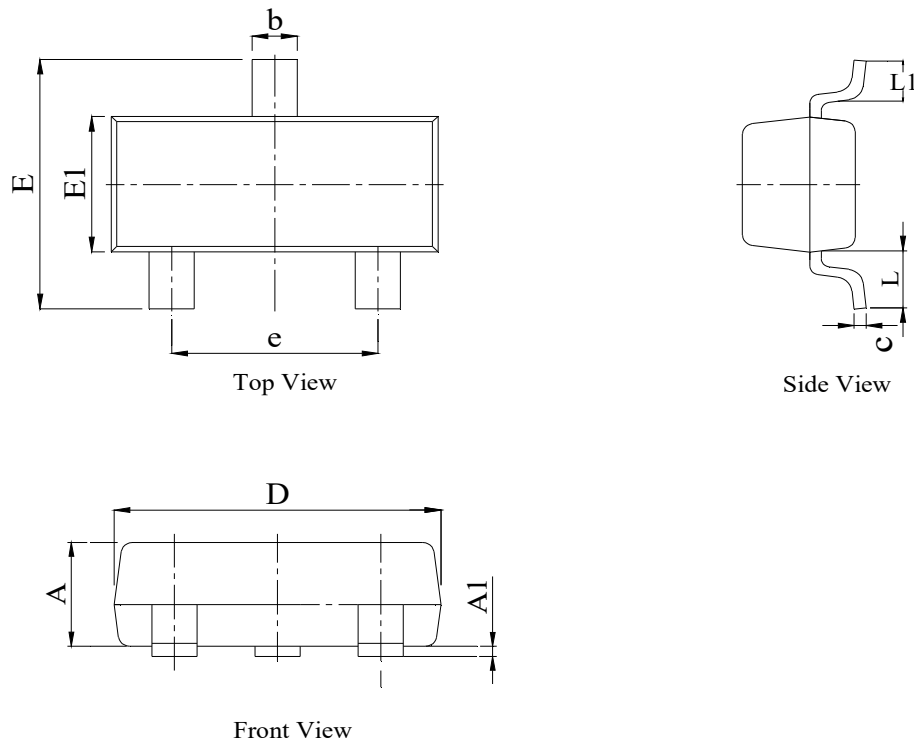
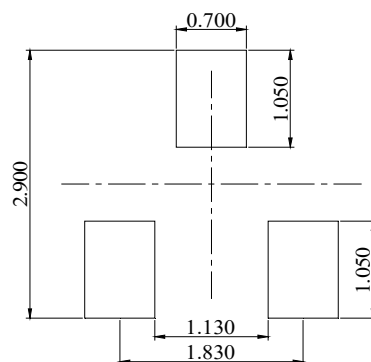


Figure 11: Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information
Package Outline


DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	-	0.10
D	2.80	2.90	3.00
E	2.25	2.40	2.55
E1	1.20	1.30	1.40
L	0.45	0.55	0.65
L1	0.20	-	0.55
b	0.30	0.40	0.50
c	-	0.10	0.15
e	-	1.90	-

Recommended Footprint


DIMENSIONS: MILLIMETERS

单击下面可查看定价，库存，交付和生命周期等信息

[>>JW\(捷捷微\)](#)